

NLAS324

Dual SPST Analog Switch, Low Voltage, Single Supply

The NLAS324 is a dual SPST (Single Pole, Single Throw) switch, similar to 1/2 a standard 4066. The device permits the independent selection of 2 analog/digital signals. Available in the Ultra-Small 8 package.

The use of advanced 0.6μ CMOS process, improves the R_{ON} resistance considerably compared to older higher voltage technologies.

Features

- On Resistance is 20Ω Typical at 5.0 V
- Matching is $< \Omega$ Between Sections
- 2 – 6 V Operating Range
- Ultra Low $< 5 \text{ pC}$ Charge Injection
- Ultra Low Leakage $< 1 \text{ nA}$ at 5.0 V, 25°C
- Wide Bandwidth $> 200 \text{ MHz}$, -3 dB
- 2000 V ESD (HBM)
- R_{ON} Flatness $\pm 6 \Omega$ at 5.0 V
- US8 Package
- Negative Enable
- Switches are Independent
- Pb-Free Package is Available

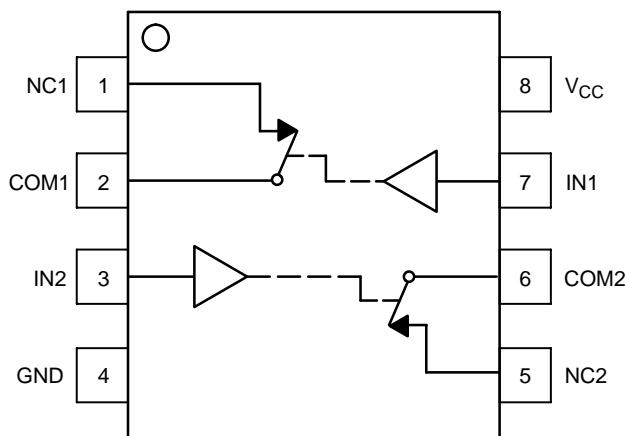


Figure 1. Pinout



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MARKING DIAGRAM



A7 = Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

PIN ASSIGNMENT

1	NC1
2	COM1
3	IN2
4	GND
5	NC2
6	COM2
7	IN1
8	V _{CC}

FUNCTION TABLE

On/Off Enable Input	State of Analog Switch
L	On
H	Off

ORDERING INFORMATION

Device	Package	Shipping [†]
NLAS324US	US8	3,000 / Tape & Reel
NLAS324USG	US8 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage	-0.5 to +7.0	V
I_{IK}	DC Input Diode Current $V_I < GND$	-50	mA
I_{OK}	DC Output Diode Current $V_O < GND$	-50	mA
I_O	DC Output Sink Current	± 50	mA
I_{CC}	DC Supply Current per Supply Pin	± 100	mA
I_{GND}	DC Ground Current per Ground Pin	± 100	mA
T_{STG}	Storage Temperature Range	-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T_J	Junction Temperature under Bias	+150	°C
θ_{JA}	Thermal Resistance (Note 1)	250	°C/W
P_D	Power Dissipation in Still Air at 85°C	250	mW
MSL	Moisture Sensitivity	Level 1	
F_R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 150 N/A	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V_{CC}	Positive DC Supply Voltage	2.0	5.5	V
V_{IN}	Digital Input Voltage (Enable)	GND	5.5	V
V_{IO}	Static or Dynamic Voltage Across an Off Switch	GND	V_{CC}	V
V_{IS}	Analog Input Voltage (NO, COM)	GND	V_{CC}	V
T_A	Operating Temperature Range, All Package Types	-55	+125	°C
t_r, t_f	Input Rise or Fall Time, (Enable Input) $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

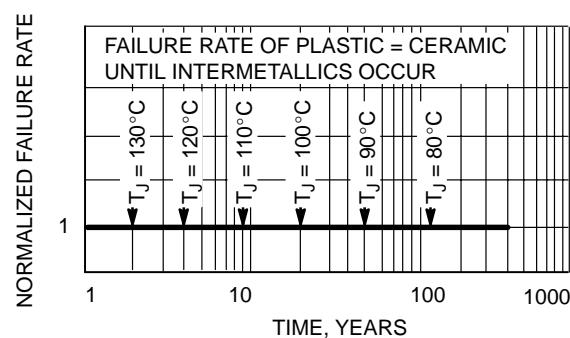


Figure 2. Failure Rate vs. Time Junction Temperature

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DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V _{CC}	Guaranteed Max Limit			Unit	
				-55 to 25°C	<85°C	<125°C		
V _{IH}	Minimum High-Level Input Voltage, Enable Inputs		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	V	
V _{IL}	Maximum Low-Level Input Voltage, Enable Inputs		2.0 3.0 4.5 5.5	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	V	
I _{IN}	Maximum Input Leakage Current, Enable Inputs	V _{IN} = 5.5 V or GND	0 V to 5.5 V		±0.1	±1.0	±1.0	µA
I _{CC}	Maximum Quiescent Supply Current (per package)	Enable and V _{IS} = V _{CC} or GND	5.5	1.0	1.0	2.0	µA	

DC ELECTRICAL CHARACTERISTICS – Analog Section

Symbol	Parameter	Condition	V _{CC}	Guaranteed Max Limit			Unit
				-55 to 25°C	<85°C	<125°C	
R _{ON}	Maximum ON Resistance (Figures 8 – 12)	V _{IN} = V _{IH} V _{IS} = V _{CC} to GND I _{IS} = ≤10.0mA	3.0 4.5 5.5	45 30 25	50 35 30	55 40 35	Ω
R _{FLAT(ON)}	ON Resistance Flatness	V _{IN} = V _{IH} I _{IS} = ≤10.0mA V _{IS} = 1V, 2V, 3.5V	4.5	4	4	5	Ω
I _{NO(OFF)}	Off Leakage Current, Pin 2 (Figure 3)	V _{IN} = V _{IL} V _{NO} = 1.0 V, V _{COM} = 4.5 V or V _{COM} = 1.0 V and V _{NO} 4.5 V	5.5	1	10	100	nA
I _{COM(OFF)}	Off Leakage Current, Pin 1 (Figure 3)	V _{IN} = V _{IL} V _{NO} = 4.5 V or 1.0 V V _{COM} = 1.0 V or 4.5 V	5.5	1	10	100	nA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Test Conditions	V _{CC} (V)	Guaranteed Max Limit						Unit	
				-55 to 25°C			<85°C				
				Min	Typ	Max	Min	Typ	Max		
t _{ON}	Turn-On Time	R _L = 300 Ω, C _L = 35 pF (Figures 4, 5, and 13)	2.03.04.55.5	7.0 5.0 4.5 4.5	14 10 9 9		16 12 11 11		16 12 11 11	ns	
t _{OFF}	Turn-Off Time	R _L = 300 Ω, C _L = 35 pF (Figures 4, 5, and 13)	2.03.04.5 5.5	11.0 7.0 5.0 5.0	22 14 10 10		24 16 12 12		24 16 12 12	ns	

				Typical @ 25, V _{CC} = 5.0 V							
C _{IN} C _{NO} or C _{NC} C _{COM(OFF)} C _{COM(ON)}	Maximum Input Capacitance, Select Input Analog I/O (switch off) Common I/O (switch off) Feedthrough (switch on)			8 10 10 20						pF	

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ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Condition	V _{CC}	Limit	Unit
			V	25°C	
BW	Maximum On-Channel -3dB Bandwidth or Minimum Frequency Response	V _{IS} = 0 dBm V _{IS} centered between V _{CC} and GND (Figures 6 and 14)	3.0 4.5 5.5	190 200 220	MHz
V _{ONL}	Maximum Feedthrough On Loss	V _{IS} = 0 dBm @ 10 kHz V _{IS} centered between V _{CC} and GND (Figure 6)	3.0 4.5 5.5	-2 -2 -2	dB
V _{IISO}	Off-Channel Isolation	f = 100 kHz; V _{IS} = 1 V RMS V _{IS} centered between V _{CC} and GND (Figures 6 and 15)	3.0 4.5 5.5	-93	dB
Q	Charge Injection Enable Input to Common I/O	V _{IS} = V _{CC} to GND, f _{IS} = 20 kHz t _r = t _f = 3 ns R _{IS} = 0 Ω, C _L = 1000 pF Q = C _L * ΔV _{OUT} (Figures 7 and 16)	3.0 5.5	1.5 3.0	pC
THD	Total Harmonic Distortion THD + Noise	F _{IS} = 20 Hz to 1 MHz, R _L = R _{gen} = 600 Ω, C _L = 50 pF V _{IS} = 3.0 V _{PP} sine wave V _{IS} = 5.0 V _{PP} sine wave (Figure 17)	3.3 5.5	0.3 0.15	%

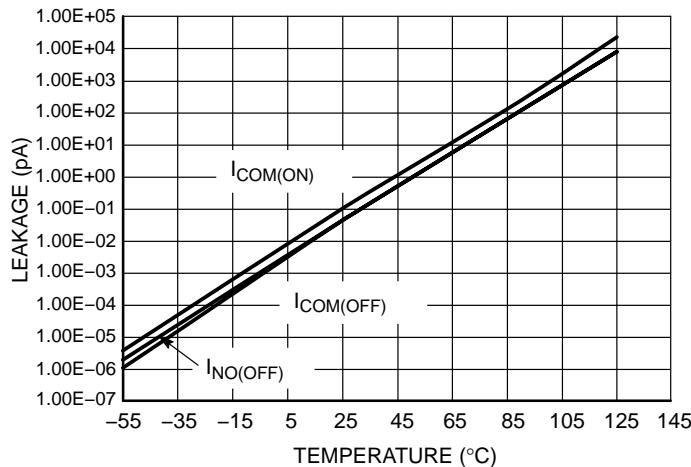


Figure 3. Switch Leakage vs. Temperature

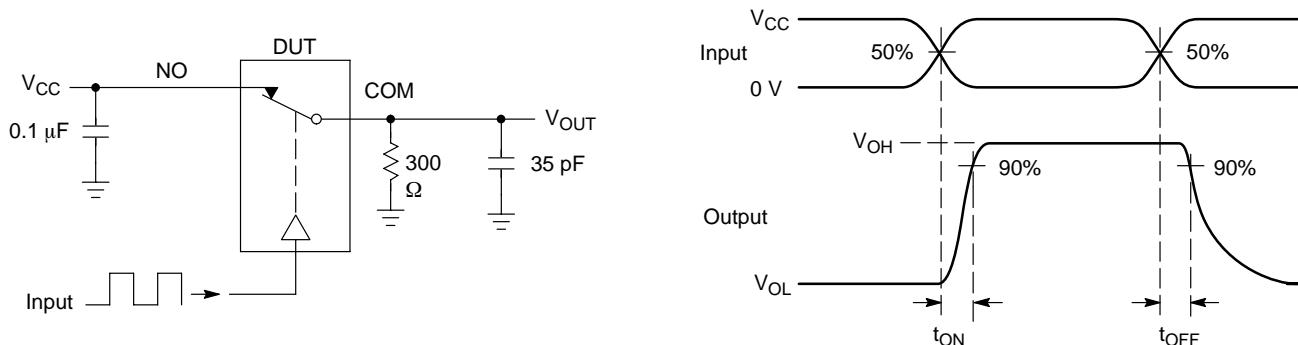


Figure 4. t_{ON}/t_{OFF}

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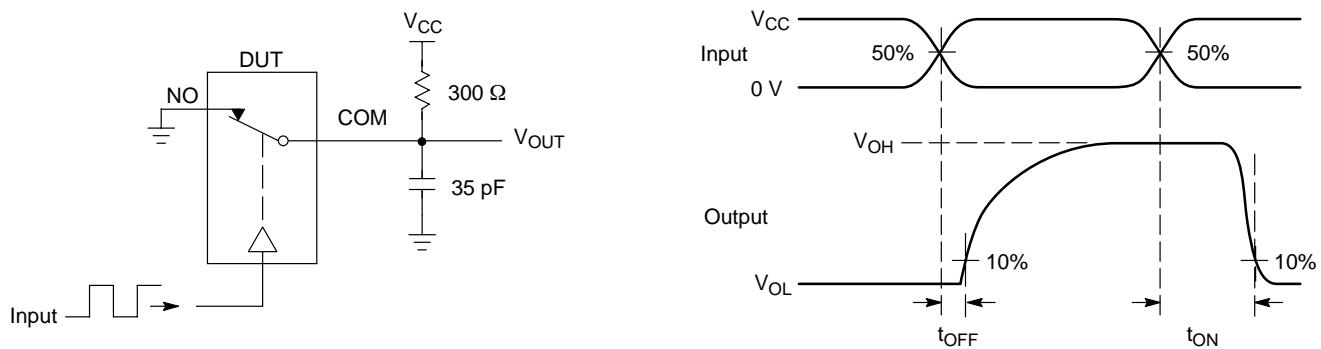
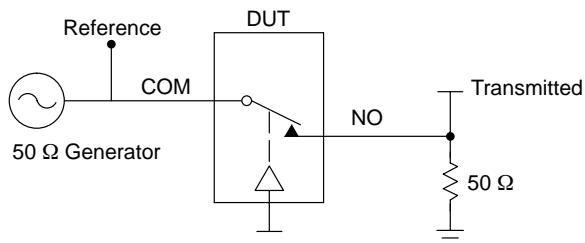


Figure 5. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO}, Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO} = \text{Off Channel Isolation} = 20 \log \left(\frac{V_{OUT}}{V_{IN}} \right) V_{IN} \text{ at } 100 \text{ kHz}$$

$$V_{ONL} = \text{On Channel Loss} = 20 \log \left(\frac{V_{OUT}}{V_{IN}} \right) V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

**Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk
(On Channel to Off Channel)/V_{ONL}**

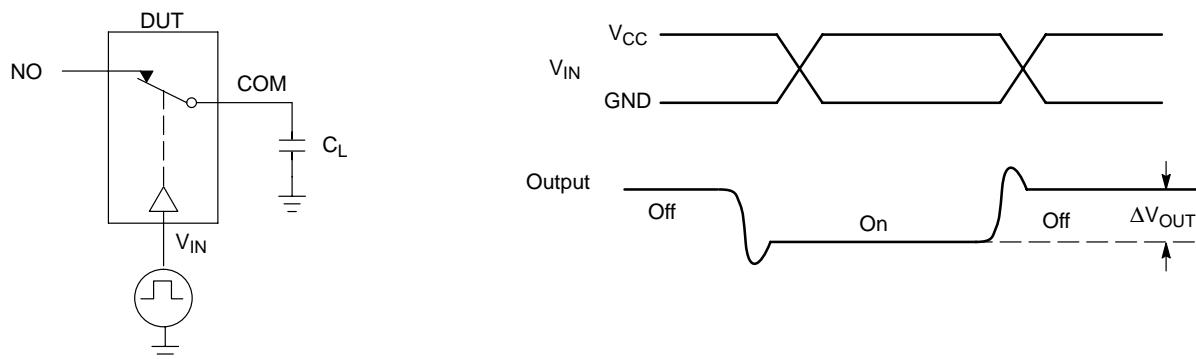


Figure 7. Charge Injection: (Q)

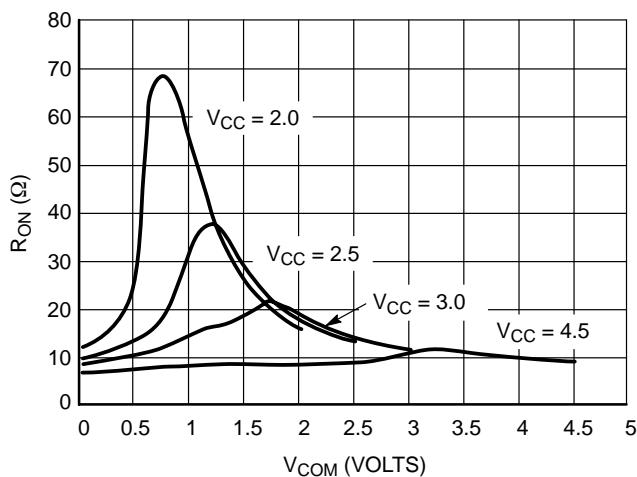


Figure 8. R_{ON} vs. V_{COM} and V_{CC} (@25°C)

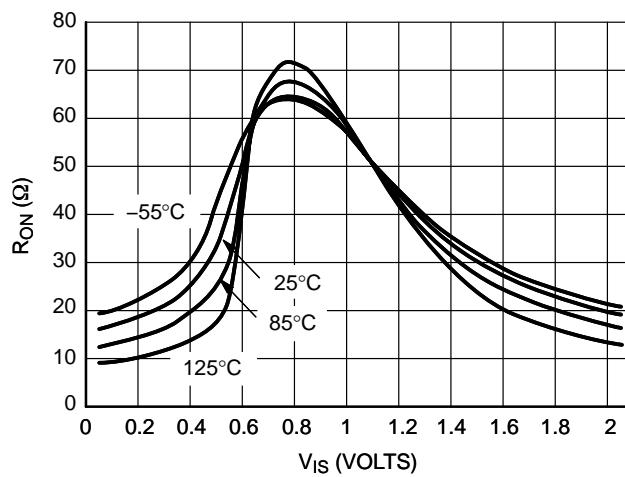


Figure 9. R_{ON} vs. V_{COM} and Temperature,
 $V_{CC} = 2.0$ V

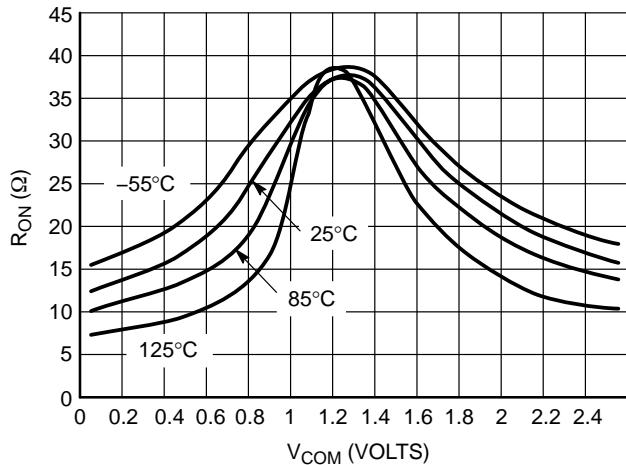


Figure 10. R_{ON} vs. V_{COM} and Temperature,
 $V_{CC} = 2.5$ V

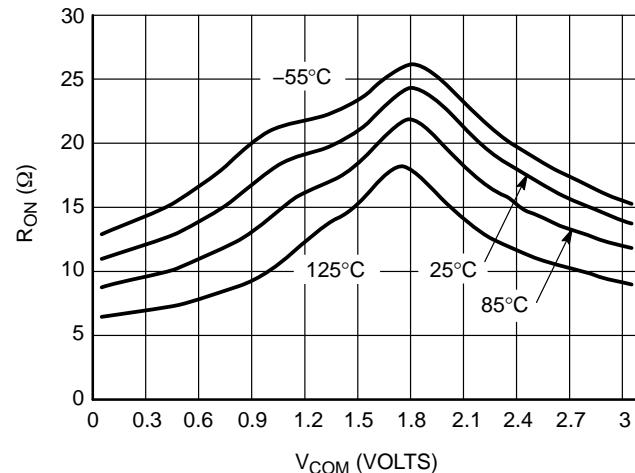


Figure 11. R_{ON} vs. V_{COM} and Temperature,
 $V_{CC} = 3.0$ V

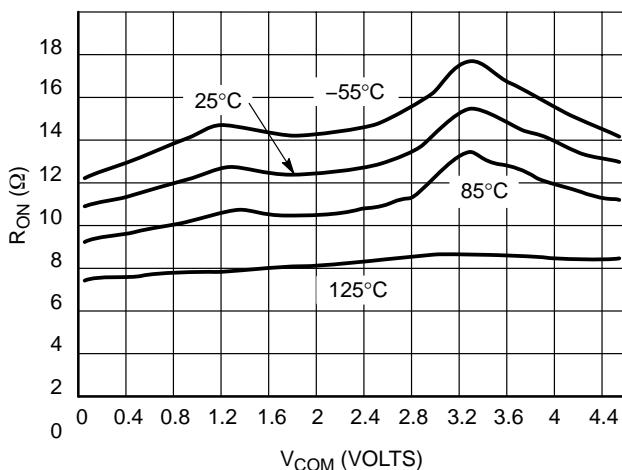


Figure 12. R_{ON} vs. V_{COM} and Temperature,
 $V_{CC} = 4.5$ V

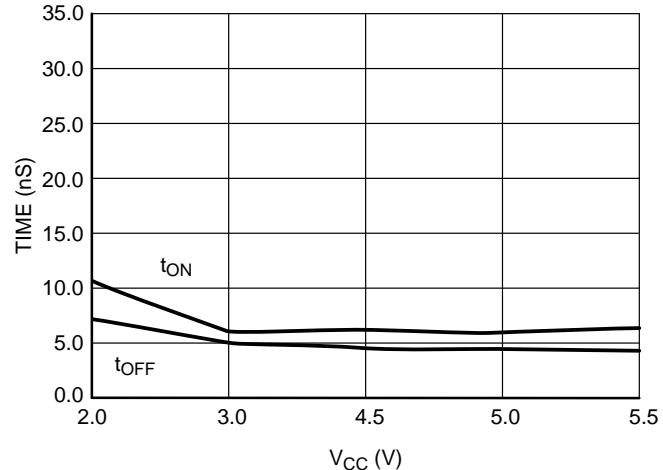
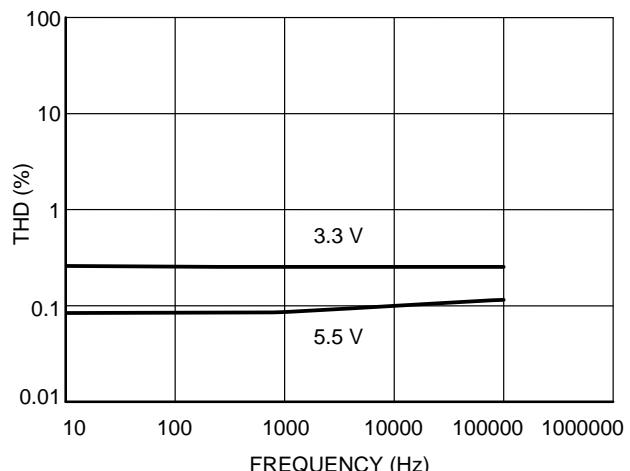
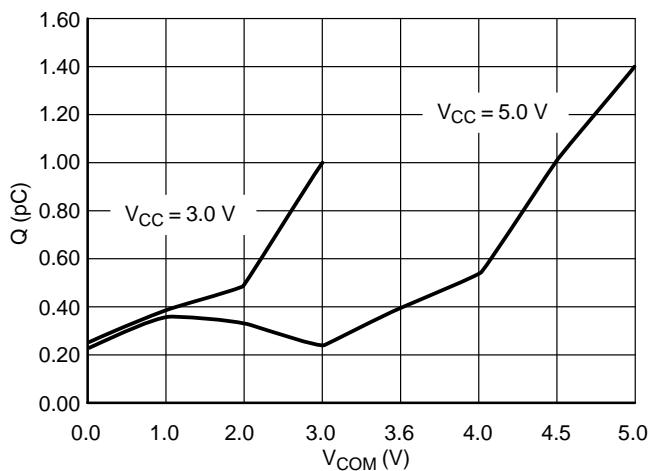
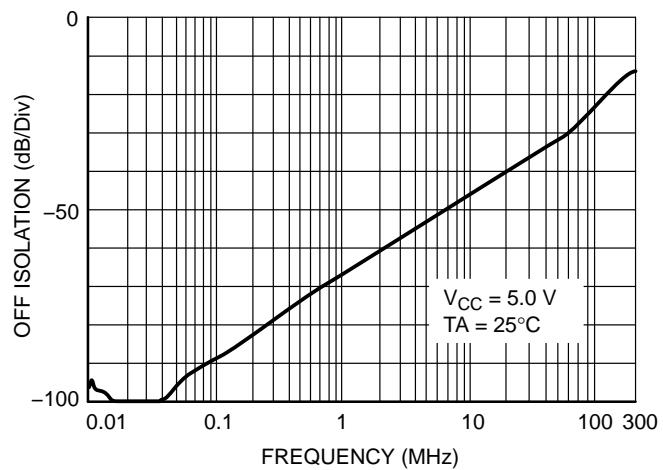
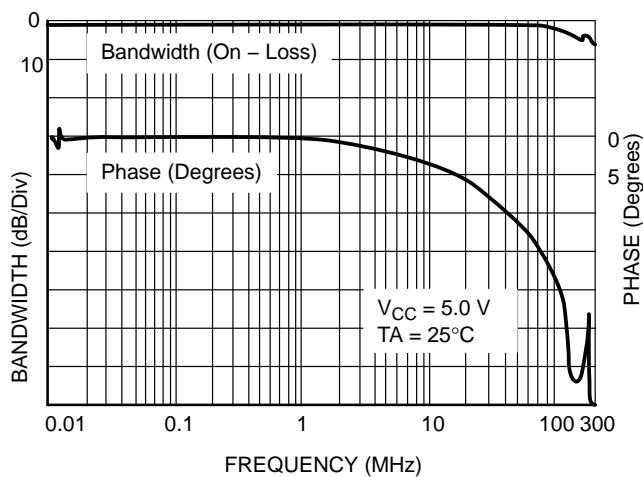


Figure 13. Switching Time vs. Supply Voltage,
 $T = 25^\circ C$

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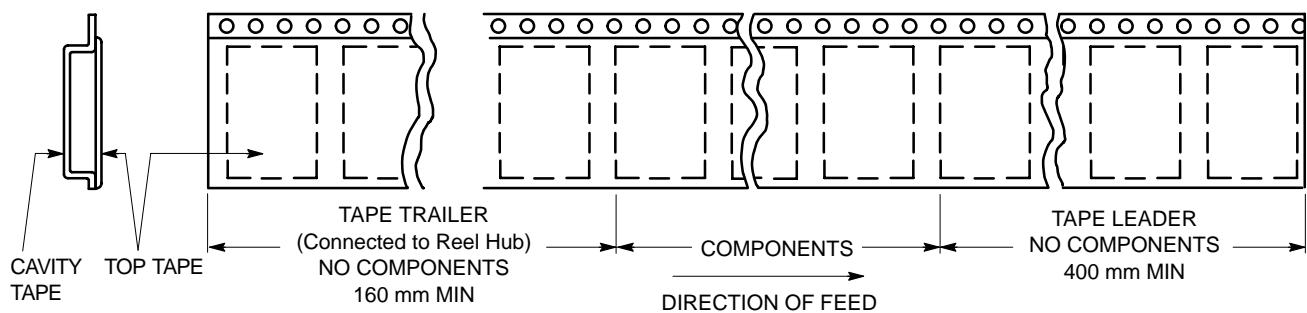


Figure 18. Tape Ends for Finished Goods

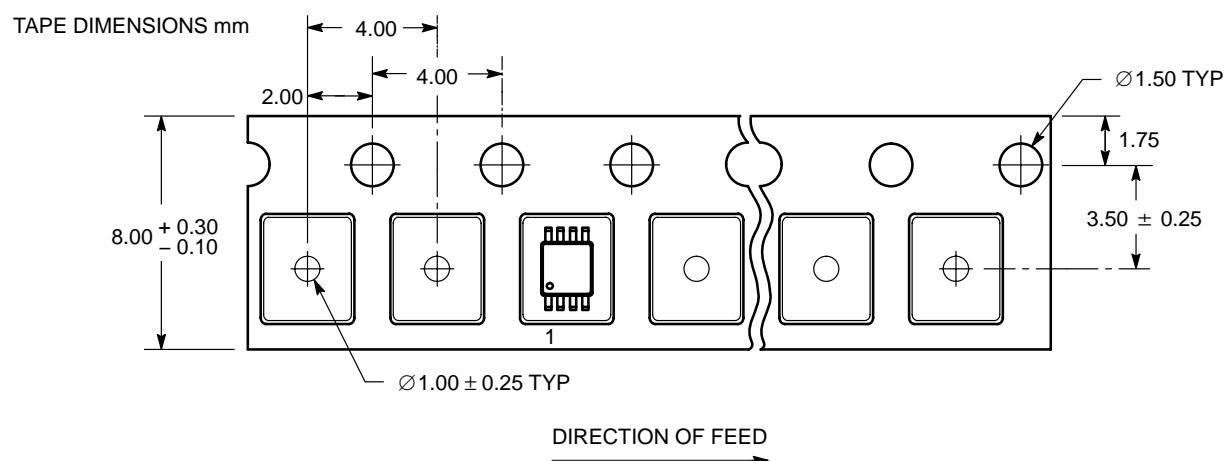


Figure 19. US8 Reel Configuration/Orientation

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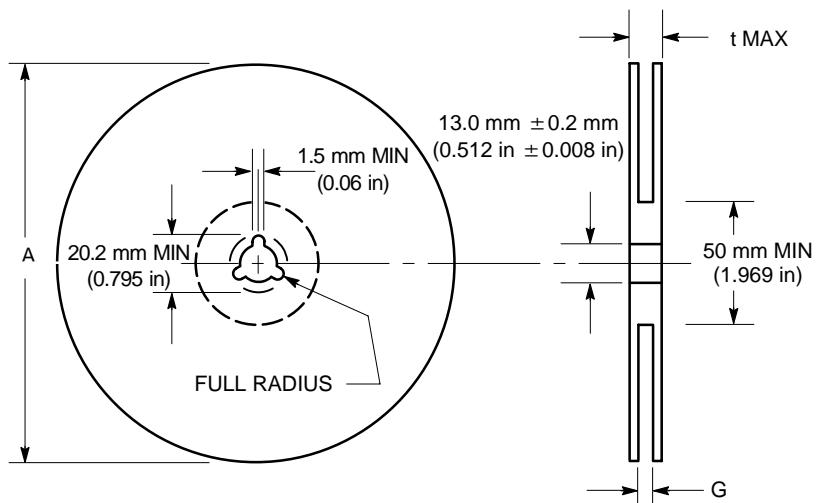


Figure 20. Reel Dimensions

REEL DIMENSIONS

Tape Size	T and R Suffix	A Max	G	t Max
8 mm	US	178 mm (7 in)	8.4 mm, + 1.5 mm, -0.0 (0.33 in + 0.059 in, -0.00)	14.4 mm (0.56 in)

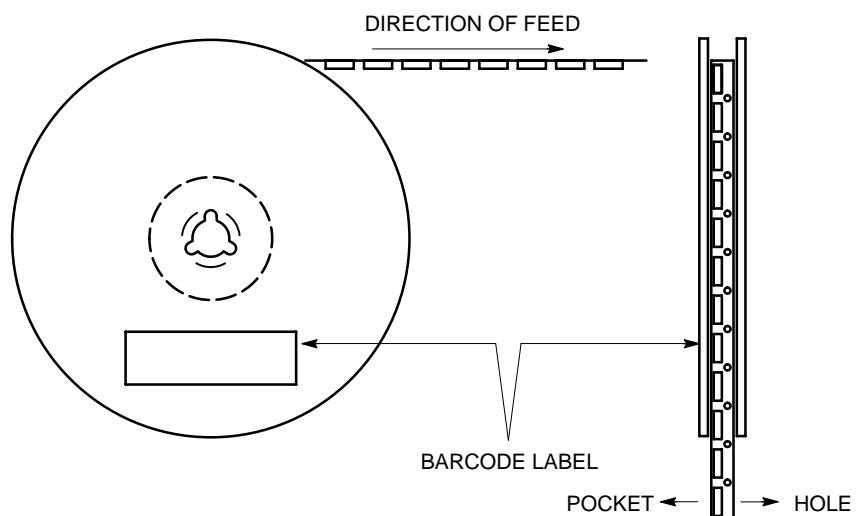
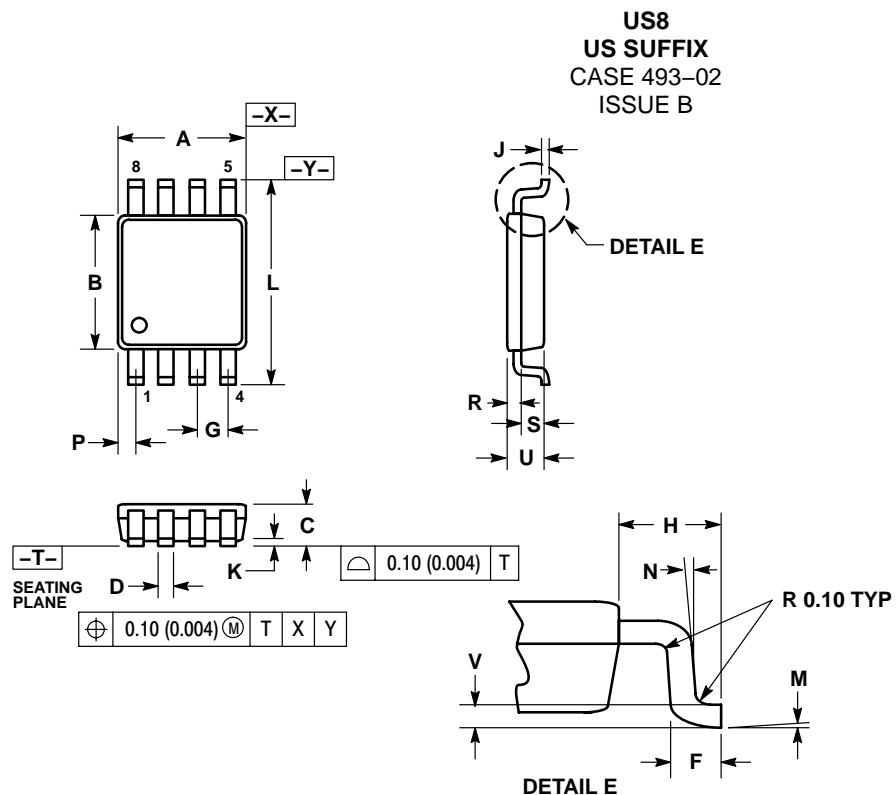


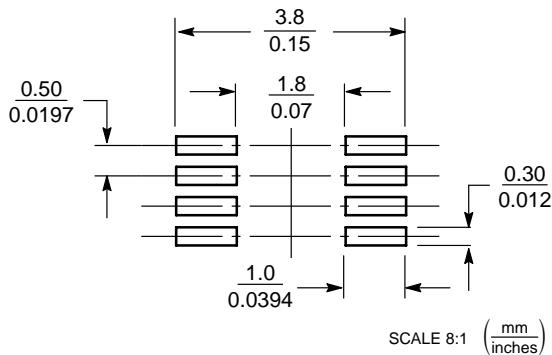
Figure 21. Reel Winding Direction

PACKAGE DIMENSIONS



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.90	2.10	0.075	0.083
B	2.20	2.40	0.087	0.094
C	0.60	0.90	0.024	0.035
D	0.17	0.25	0.007	0.010
F	0.20	0.35	0.008	0.014
G	0.50 BSC		0.020 BSC	
H	0.40 REF		0.016 REF	
J	0.10	0.18	0.004	0.007
K	0.00	0.10	0.000	0.004
L	3.00	3.20	0.118	0.126
M	0 $^{\circ}$	6 $^{\circ}$	0 $^{\circ}$	6 $^{\circ}$
N	5 $^{\circ}$	10 $^{\circ}$	5 $^{\circ}$	10 $^{\circ}$
P	0.23	0.34	0.010	0.013
R	0.23	0.33	0.009	0.013
S	0.37	0.47	0.015	0.019
U	0.60	0.80	0.024	0.031
V	0.12 BSC		0.005 BSC	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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